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Manufacturers of World Class Discrete Semiconductors  
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**1N3595**

**SILICON LOW LEAKAGE DIODE**

**JEDEC DO-35 CASE**

### DESCRIPTION

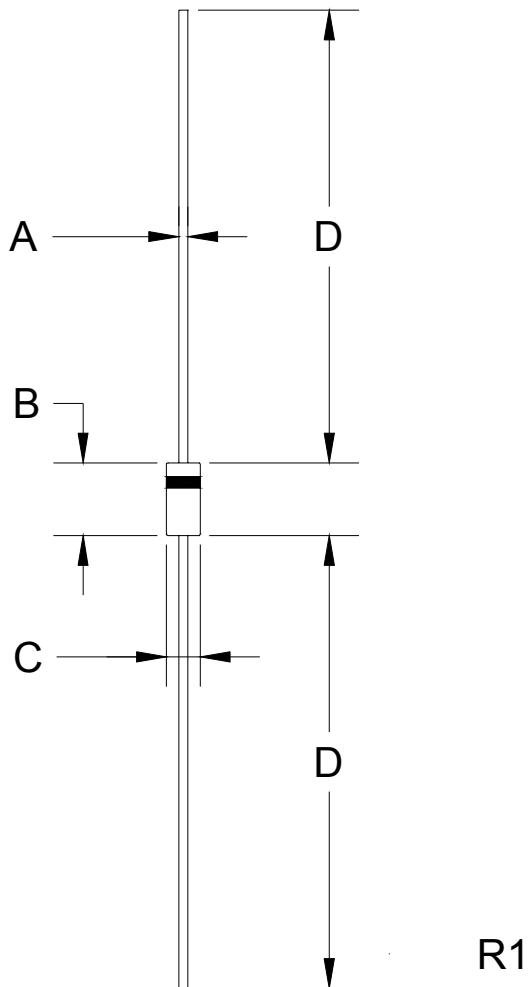
The CENTRAL SEMICONDUCTOR 1N3595 is an epitaxial planar silicon diode designed for low leakage, high conductance applications. Higher breakdown voltage devices are available on special order.

### MAXIMUM RATINGS: ( $T_A=25^\circ\text{C}$ )

	<u>SYMBOL</u>		<u>UNITS</u>
Peak Repetitive Reverse Voltage	$V_{RRM}$	150	V
Peak Working Reverse Voltage	$V_{RWM}$	125	V
Average Forward Current	$I_O$	150	mA
Forward Steady-State Current	$I_F$	225	mA
Recurrent Peak Forward Current	$i_f$	600	mA
Peak Forward Surge Current (1.0s pulse)	$I_{FSM}$	500	mA
Peak Forward Surge Current (1.0μs pulse)	$I_{FSM}$	4.0	A
Power Dissipation	$P_D$	500	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +200	°C

### ELECTRICAL CHARACTERISTICS: ( $T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
$I_R$	$V_R=125\text{V}$		1.0	nA
$I_R$	$V_R=125\text{V}, T_A=125^\circ\text{C}$		500	nA
$I_R$	$V_R=125\text{V}, T_A=150^\circ\text{C}$		3.0	μA
$I_R$	$V_R=30\text{V}, T_A=125^\circ\text{C}$		300	nA
$BV_R$	$I_R=100\mu\text{A}$	150		V
$V_F$	$I_F=1.0\text{mA}$	0.54	0.69	V
$V_F$	$I_F=5.0\text{mA}$	0.62	0.77	V
$V_F$	$I_F=10\text{mA}$	0.65	0.80	V
$V_F$	$I_F=50\text{mA}$	0.75	0.88	V
$V_F$	$I_F=100\text{mA}$	0.79	0.92	V
$V_F$	$I_F=200\text{mA}$	0.83	1.0	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		8.0	pF
$t_{rr}$	$V_R=3.5\text{V}, I_f=10\text{mA}, R_L=1.0\text{k}\Omega$		3.0	μs

JEDEC DO-35 CASE - MECHANICAL OUTLINE

SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A	0.018	0.022	0.46	0.56
B	0.120	0.200	3.05	5.08
C	0.060	0.090	1.52	2.29
D	1.000	-	25.40	-

DO-35 (REV: R0)

Marking Code: C1N3595

R1